



INFORMATION DISCLOSURE CITATION  PAGE 1 OF 3				Atty Docket No. OPE-026	Serial No. 10/700,016		
				Applicant Geoff W. Taylor et al.			
				Filed November 3, 2003	Group <u>2813</u>		
US PATENT DOCUMENTS							
Examiner Initials		Document No.	Date	Name	Class	Sub-class	Filing date if approp.
<u>MDT</u>	A	3,919,656	11/11/75	Sokal et al.	330	51	—
	B	4,424,525	1/3/84	Mimura	357	23	—
	C	4,658,403	4/14/87	Takiguchi et al.	372	96	—
	D	4,683,484	7/28/87	Derkits, Jr.	357	16	—
	E	4,806,997	2/21/89	Simmons et al.	357	16	—
	F	4,814,774	3/21/89	Herczfeld	342	372	—
	G	4,827,320	5/2/89	Morkoc et al.	357	22	—
	H	4,829,272	5/9/89	Kameya	333	139	—
	I	4,899,200	2/6/90	Shur et al.	357	30	—
	J	4,949,350	8/14/90	Jewell et al.	372	45	—
	K	5,010,374	4/23/91	Cooke et al.	357	16	—
	L	5,105,248	4/14/92	Burke et al.	357	24	—
	M	5,202,896	4/13/93	Taylor	372	50	—
	N	5,337,328	8/9/94	Lang et al.	372	45	—
	O	5,386,128	1/31/95	Fossum et al.	257	183.1	—
	P	5,422,501	6/6/95	Bayraktaroglu	257	195	—
	Q	5,436,759	7/25/95	Dijaili et al.	359	333	—
	R	5,698,900	12/16/97	Bozada et al.	257	744	—
	S	6,031,243	2/29/00	Taylor	257	13	—
	T	6,043,519	3/28/00	Shealy et al.	257	195	—
	U	US 20020067877	6/6/02	Braun et al.			—
	V	5,288,659	02/94	Koch et al.	438	31	—
	W	5,452, 118	09/95	Maruska	398	204	—
↓	X	5,999,553	12/99	Sun,	372	50	—
EXAMINER <u>Monica D. Dawson</u>				DATE CONSIDERED <u>4/15/05</u>			



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US PATENT DOCUMENTS							
Examiner Initials	Document No.	Date	Name	Class	Sub-class	Filing date if approp.	
M D K	A 6,479,844	11/02	Taylor	257	98	—	
	B 6,720,584	04/04	Hata et al.	257	98	—	
	C 6,483,170	11/19/02	Johansson	257	580	—	
	D 6,239,475	05/29/01	Johansson et al.	257	488	—	
	E 6,037,616	03/12/00	Amamiya	257	198	—	
Y	F 5,003,366	03/26/91	Mishimi et al.	257	197	—	
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X							
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OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)				
MDH	AA	10-Gb/s High-Speed Monolithically Integrated photoreceiver Using InGaAs p-i-n PD and Planar Doped InAlAs/InGaAs HEMT's by Akahori et al, IEEE Photonics Technology Letters, Vol 4, No. 7, July 1992		
	BB	10-Gbit/s InP-Based High-Performance Monolithic Photoreceivers Consisting of p-i-n Photodiodes and HEMT's by Takahata et al., IEICE Trans. Electron., Vol. E83-C, No. 6 June 2000		
	CC	10 Ghz Bandwidth Monolithic p-i-n Modulation-doped Field Effect Transistor Photoreceiver by Dutta et al., Appl. Phys. Lett., Vol. 63, No. 15, 11 October 1993		
	DD	20 Gbit/s Long Wavelength Monolithic Integrated Photoreceiver Grown on GaAs by Hurm, et al., Electronics Letters, Vol. 33, No. 7, 27th March 1997		
	EE	Monolithic Integrated Optoelectronic Circuits by Berroth et al., Fraunhofer Institute for Applied Solid State Physics (IAF), Germany, IEEE 1995		
	FF	Heterojunction Field-Effect Transistor (HFET), Reprinted from Electronics Letters, Vol 22, No. 15, pp. 784-786, 17th July 1986		
	GG	High Temperature Annealing of Modulation Doped GaAs/A1GaAs Heterostructures for FET Applications by Lee et al., 1983 IEEE/Cornell Conf. On High-Speed Semiconductor Devices & Ckts, 8/83		
	HH	Submicrometre Gate Length Scaling of Inversion Channel Heterojunction Field Effect Transistor by Kiely et al., Electronics Letters, Vol. 30, No. 6 17th March 1994		
	II	Theoretical and Experimental Results for the Inversion Channel Heterostructure Field Effect Transistor by Taylor et al., IEE Proceedings-G, Vol. 140, No. 6, December 1993		
	jj	Transmitting Transistor Design: RF Transmitting Transistor and power amplifier fundamentals, Phillips Semiconductors; March 23, 1998		
	kk	Thermally Stable Ohmic Contacts to n-type GaAs. VIII. Sputter-deposited InAs Contacts: HJ Kim, Masanori Murakami, SL Wright, M. Norcott, WH Price and D. La Tulipe; 4/11/90		
	II	Thermally Stable Ohmic Contact to n-type GaAs IX. Sputter-deposited InAS Contacts NiIn(mn) and NiIn(w) Contact Metals, J. Applied Physics, Vol. 70, 11/12/91 pgs. 7443-7448		
	mm	Transferred Substrate HBT's with 254 GH2F. D. Mensa et al.; Electron Lett. 4/99; 35(7) pp. 605-606		
EXAMINER Donald D. Dawson		DATE CONSIDERED 4/5/05		